

**AMENDMENT TO THE SPECIFICATION**

Please amend the paragraph beginning on page 3, line 13 as follows:

--As a substrate for GaN based crystal, sapphire, SiC, NGO, etc., are used; however, none of these substrates have the lattice constant that matches that of GaN, making it difficult to obtain coherent growth. Therefore, in a GaN layer that has been grown on such a substrate, a large number of dislocations (edge dislocations, screw dislocations, mixed dislocations) exist. For example, when a sapphire substrate is used, there exist approximately  $1 [[?]] \times 10^9 \text{ cm}^{-2}$  dislocations. These dislocations decrease the luminous efficiency of an ultraviolet light emitting diode.--

Please amend the paragraph beginning on page 4, line 4 as follows:

--Fig. 9 is a partial enlarged view of Fig. 8 schematically showing the distribution of the dislocations in a GaN crystal that has been obtained by ELO. As shown in this figure, in the u-GaN layer 43, a large number of dislocations exist in the region X<sub>1</sub> located above the seed crystal 42, wherein the dislocation density thereof is approximately  $1 [[?]] \times 10^9 \text{ cm}^{-2}$ . In contrast, the region X<sub>2</sub> located on the dielectric mask 54 has fewer dislocations, wherein the dislocation density thereof is decreased to approximately  $1 [[?]] \times 10^7 \text{ cm}^{-2}$ . In this GaN crystal, the width of the dielectric mask 54 is approximately 4 μm and the interval therebetween is approximately 12 μm. As described above, employing ELO makes it possible to form a crystal on the dielectric mask 54 that has a low dislocation density, reducing the crystal defects and improving the luminous efficiency of the ultraviolet light emitting diode. An example of a semiconductor light emitting device that has a region of low dislocation density, other than that described above, is disclosed in the specification of the European Patent Publication No. 1104031.--

Please amend the paragraph beginning on page 10, line 18 as follows:

--As described above, the concave portions 121 positioned beneath the light-shielding portions of the base electrode 21 and n-type electrode 24 have widths and intervals different [[form]] from those positioned beneath the emission detection surface. In other words, the concave portions 121 positioned beneath the light-shielding region  $L_1$  where the base electrode 21 is formed and the light-shielding region  $L_2$  where wire bonding is applied to the n-type electrode 24 have a smaller width than the other concave portions 121, i.e., those positioned beneath the region  $L_3$  serving as an emission detection surface. The reason for this will be described in detail below; however, in brief, this is because the regions  $L_1$  and  $L_2$  have light shielding properties, and therefore, even when the dislocation density of the crystals below these region is high, it does not affect emission intensity; while it is necessary to enhance the mechanical strength of the structure of these crystals because wire bonding is applied to the regions  $L_1$  and  $L_2$ . In contrast, it is necessary to make the dislocation density of the crystal positioned beneath the region  $L_3$  low in order to enhance emission intensity, and therefore the width of these concave portions 121 is increased.--

Please amend the paragraph beginning on page 11, line 16 as follows:

--Given the above consideration, it is preferable that the width  $\beta$  of the concave portions 121 beneath the region  $L_3$  be at least twice that of the width  $\alpha$  of the concave portions 121 beneath regions  $L_1$  and  $L_2$ . Preferable examples of the widths of the concave portions 121 include, for example, the width  $\beta$  of the concave portions 121 beneath the region  $L_3$  being not less than 6  $\mu\text{m}$  and not more than 20  $\mu\text{m}$ , and more preferably not less than 9  $\mu\text{m}$  and not more than 12  $\mu\text{m}$ . In contrast, the width [[a]] a of the concave portions 121 positioned beneath the

regions L<sub>1</sub> and L<sub>2</sub> is preferably not less than 1  $\mu\text{m}$  and not more than 6  $\mu\text{m}$ , and more preferably not less than 2  $\mu\text{m}$  and not more than 4  $\mu\text{m}$ . Because the crystals beneath the regions L<sub>1</sub> and L<sub>2</sub> are required to have a structure having high mechanical strength, it is therefore preferable that the width [[?]]  $\gamma$  of the projecting portions 123 formed between the concave portions 121 be not less than 1  $\mu\text{m}$  and not more than 6  $\mu\text{m}$ , and more preferably not less than 2  $\mu\text{m}$  and not more than 4  $\mu\text{m}.$ --